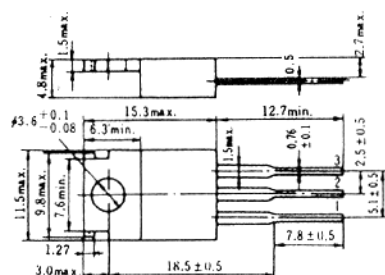


2SB857, 2SB858

SILICON PNP TRIPLE DIFFUSED

LOW FREQUENCY POWER AMPLIFIER

COMPLEMENTARY PAIR WITH 2SD1133 AND 2SD1134



1. Base
 2. Collector
(Flange)
 3. Emitter
- (Dimensions in mm)

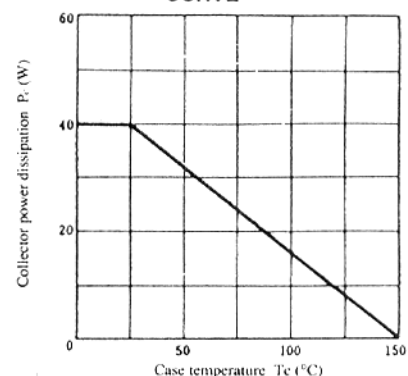
(JEDEC TO-220AB)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SB857	2SB858	Unit
Collector to base voltage	V _{CB0}	-70	-70	V
Collector to emitter voltage	V _{CEO}	-50	-60	V
Emitter to base voltage	V _{EB0}	-5	-5	V
Collector current	I _C	-4	-4	A
Collector peak current	i _{C(peak)}	-8	-8	A
Collector power dissipation	P _{C*}	40	40	W
Junction temperature	T _j	150	150	°C
Storage temperature	T _{stg}	-45 to +150	-45 to +150	°C

* Value at T_c = 25°C

MAXIMUM COLLECTOR DISSIPATION CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition		2SB857			2SB858			Unit
				min.	typ.	max.	min.	typ.	max.	
Collector to base breakdown voltage	V _{(BR)CBO}	I _C = -10μA, I _E = 0		-70	—	—	-70	—	—	V
Collector to emitter breakdown voltage	V _{(BR)CEO}	I _C = -50mA, R _{BE} = ∞		-50	—	—	-60	—	—	V
Emitter to base breakdown voltage	V _{(BR)EBO}	I _E = -10μA, I _C = 0		-5	—	—	-5	—	—	V
Collector cutoff current	I _{CBO}	V _{CB} = -50V, I _E = 0		—	—	-1	—	—	-1	μA
DC current transfer ratio	h _{FE1} *	V _{CE} = -4V	I _C = -1A**	60	—	320	60	—	320	
	h _{FE2}		I _C = -0.1A**	35	—	—	35	—	—	
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = -2A, I _B = -0.2A**		—	—	-1	—	—	-1	V
Base to emitter voltage	V _{BE}	V _{CE} = -4V, I _C = -1A**		—	—	-1	—	—	-1	V
Gain bandwidth product	f _T	V _{CE} = -4V, I _C = -0.5A**		—	15	—	—	15	—	MHz

* The 2SB857 and 2SB858 are grouped by h_{FE1} as follows.

** Pulse Test

B	C	D
60 to 120	100 to 200	160 to 320

2SB857, 2SB858

